## MO8009

## **High Frequency, Low Power Oscillator**



#### **Features**

- Any frequency between 115 MHz and 137 MHz accurate to 6 decimal places
- 100% pin-to-pin drop-in replacement to quartz-based XO
- Excellent total frequency stability as low as ±20 ppm
- Operating temperature from -40°C to +85°C. For +125°C and/or -55°C options, refer to MO8919 and MO8921
- Low power consumption of +4.9 mA typical at 125 MHz, +1.8V
- Standby mode for longer battery life
- Fast startup time of 5 ms
- LVCMOS/HCMOS compatible output
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- Instant samples with Time Machine II and field programmable oscillators
- For AEC-Q100 oscillators, refer to MO8924 and MO8925

#### **Applications**

- Ideal for GPON/GPON, network switches, routers. servers, embedded systems
- Ideal for Ethernet, PCI-E, DDR, etc.





Pb-Free

RoHS Compliant

## **Electrical Specifications**

#### **Table 1. Electrical Characteristics**

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at +25°C and nominal supply voltage.

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition	
Frequency Range							
Output Frequency Range	f	115	-	137	MHz		
Frequency Stability and Aging							
		-20	-	+20	ppm	Inclusive of Initial tolerance at +25°C, 1st year aging at +25°C,	
Frequency Stability	F_stab	-25	-	+25	ppm	and variations over operating temperature, rated power supply	
		-50	-	+50	ppm	voltage and load.	
	Operating Temperature Range						
Operating Temperature Range	T use	-20	-	+70	°C	Extended Commercial	
Operating reinperature (tange	1_030	-40		+85	°C	Industrial	
	1	Sı	ipply Voltag	e and Curre	ent Consur	nption	
		+1.62	+1.8	+1.98	V		
		+2.25	+2.5	+2.75	V		
Supply Voltage	Vdd	+2.52	+2.8	+3.08	V	Contact KDS for +1.5V support	
Cuppi, remage		+2.7	+3.0	+3.3	V	Gontact NDG 101 11.0 V Support	
		+2.97	+3.3	+3.63	V		
		+2.25	-	+3.63	V		
	Idd		_	+6.2	+7.5	mA	No load condition, f = 125 MHz,
Current Consumption						Vdd = +2.8V, +3.0V, +3.3V or +2.25 to +3.63V	
		-	+5.5	+6.4	mA	No load condition, f = 125 MHz, Vdd =+2.5V	
		-	+4.9	+5.6	mA	No load condition, f = 125 MHz, Vdd = +1.8V	
OE Disable Current	I_OD	-	_	+4.2	mA	Vdd = +2.5V to +3.3V, OE = GND, Output in high-Z state	
		-	-	+4.0	mA	Vdd = +1.8V, OE = GND, Output in high-Z state	
		-	+2.6	+4.3	μA	ST = GND, Vdd = +2.8V to +3.3V, Output is weakly pulled down	
Standby Current	I_std	-	+1.4	+2.5	μΑ	ST = GND, Vdd = +2.5V, Output is weakly pulled down	
		-	+0.6	+1.3	μA	ST = GND, Vdd = +1.8V, Output is weakly pulled down	
			LVCMOS	OutputCha	aracteristic	es s	
Duty Cycle	DC	45	_	55	%	All Vdds	
	Tr, Tf	-	1.0	2.0	ns	Vdd = +2.5V, +2.8V, +3.0V or +3.3V, 20% - 80%	
Rise/Fall Time		-	1.3	2.5	ns	Vdd =+1.8V, 20% - 80%	
		-	0.8	2.0	ns	Vdd = +2.25V - +3.63V, 20% - 80%	
Output High Voltage	VOH	90%	-	-	Vdd	IOH = -4.0 mA (Vdd = +3.0V or +3.3V)	
Output Low Voltage	VOL	-	-	10%	Vdd	IOL = +4.0 mA (Vdd = +3.0V or +3.3V)	



Table 1. Electrical Characteristics (continued)

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition			
	Input Characteristics								
Input High Voltage	VIH	70%	-	-	Vdd	Pin 1, OE or ST			
Input Low Voltage	VIL	-	-	30%	Vdd	Pin 1, OE or ST			
Input Pull-up Impedance	Z_in	50	87	150	kΩ	Pin 1, OE logic high or logic low, or ST logic high			
input Fun-up impedance	2_111	2.0	-	-	ΜΩ	Pin 1, ST logic low			
			Startu	p and Resur	me Timing				
Startup Time	T_start	-	-	5.0	ms	Measured from the time Vdd reaches its rated minimum value			
Enable/Disable Time	T_oe	-	ı	122	ns	f = 137 MHz. For other frequencies, T_oe = 100 ns + 3 * cycles			
Resume Time	T_resume	-	1	5.0	ms	Measured from the time ST pin crosses 50% threshold			
				Jitter					
RMS Period Jitter	T_jitt	-	1.9	3.0	ps	f = 125 MHz, Vdd = +2.5V, +2.8V, +3.0V or +3.3V			
KW3 Feriod Sitter	1_jitt	-	1.8	4.0	ps	f = 125 MHz, Vdd = +1.8V			
Peak-to-peak Period Jitter	T_pk	-	12	25	ps	f = 125 MHz, Vdd = +2.5V, +2.8V, +3.0V or +3.3V			
reak-to-peak reflou sitter	i_pk	-	14	30	ps	f = 125 MHz, Vdd = +1.8V			
RMS Phase Jitter (random)	T_phj	-	0.5	0.9	ps	Integration bandwidth = 900 kHz to 7.5 MHz			
NWO FIIASE SILLEI (TAIIQOIII)	ı_pııj	-	1.3	2.0	ps	Integration bandwidth = 12 kHz to 20 MHz			

## **Table 2. Pin Description**

Pin	Symbol		Functionality	
	Output Enable		H <sup>[1]</sup> : specified frequency output L: output is high impedance. Only output driver is disabled.	
1	1 OE/ST/NC	Standby	$H^{[1]}\!\!:$ specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Suppl	
		No Connect	current reduces to I_std.  Any voltage between 0 and Vdd or Open <sup>[1]</sup> : Specified frequency output. Pin 1 has no function.	
2	GND	Power	Electrical ground	
3	OUT	Output	Oscillator output	
4	VDD	Power	Power supply voltage <sup>[2]</sup>	

## **Top View**

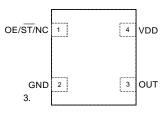


Figure 1. Pin Assignments

#### Notes:

- In OE or ST mode, a pull-up resistor of 10 kΩ or less is recommended if pin 1 is not externally driven. If pin 1 needs to be left floating, use the NC option.
- 2. A capacitor of value 0.1  $\mu F$  or higher between Vdd and GND is required.

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#### **Table 3. Absolute Maximum Limits**

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	+150	°C
Vdd	-0.5	+4.0	V
Electrostatic Discharge	-	+2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	-	+260	°C
Junction Temperature <sup>[3]</sup>	-	+150	°C

#### Note:

### Table 4. Thermal Consideration<sup>[4]</sup>

Package	θJA, 4 Layer Board (°C/W)	θJA, 2 Layer Board (°C/W)	θJC, Bottom (°C/W)
7050	142	273	30
5032	97	199	24
3225	109	212	27
2520	117	222	26
2016	152	252	36

#### Note:

## Table 5. Maximum Operating Junction Temperature<sup>[5]</sup>

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature		
+70°C	+80°C		
+85°C	+95°C		

#### Note:

## **Table 6. Environmental Compliance**

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method 2002
Mechanical Vibration	MIL-STD-883F, Method 2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method2003
Moisture Sensitivity Level	MSL1 @ 260°C

<sup>3.</sup> Exceeding this temperature for extended period of time may damage the device.

<sup>4.</sup> Refer to JESD51 for θJA and θJC definitions, and reference layout used to determine the θJA and θJC values in the above table.

<sup>5.</sup> Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.



## Test Circuit and Waveform<sup>[6]</sup>

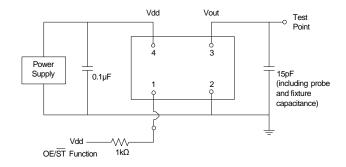


Figure 2. Test Circuit

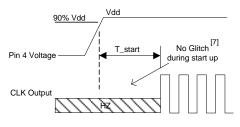
#### Note:

6. Duty Cycle is computed as Duty Cycle = TH/Period.

## 80% Vdd 50% 20% Vdd High Pulse Low Pulse (TH) Period

Figure 3. Waveform

## **Timing Diagrams**

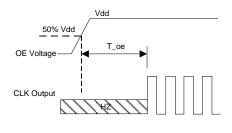


T\_start: Time to start from power-off

Vdd 50% Vdd CLK Output

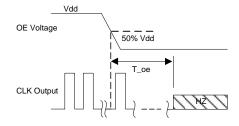
T\_resume: Time to resume from ST

Figure 4. Startup Timing (OE/ST Mode)



T\_oe: Time to re-enable the clock output

Figure 5. Standby Resume Timing (ST Mode Only)



T\_oe: Time to put the output in High Z mode

Figure 6. OE Enable Timing (OE Mode Only)

Note:

MO8009 has "no runt" pulses and "no glitch" output during startup or resume.

Figure 7. OE Disable Timing (OE Mode Only)



## Performance Plots<sup>[8]</sup>

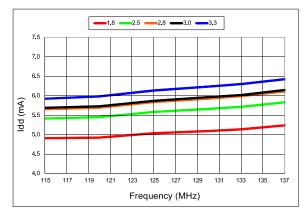


Figure 8. Idd vs Frequency

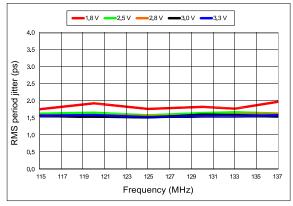


Figure 10. RMS Period Jitter vs Frequency

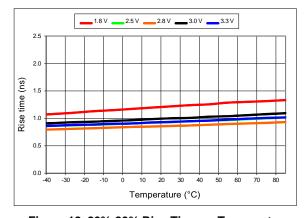


Figure 12. 20%-80% Rise Time vs Temperature

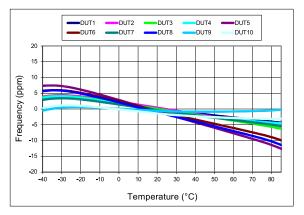


Figure 9. Frequency vs Temperature, +1.8V

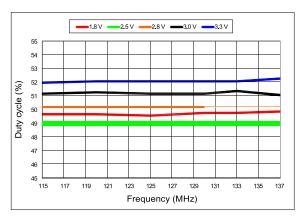


Figure 11. Duty Cycle vs Frequency

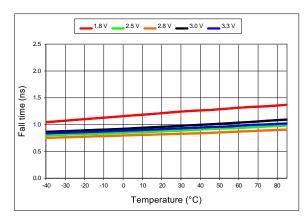


Figure 13. 20%-80% Fall Time vs Tem



## Performance Plots<sup>[8]</sup>

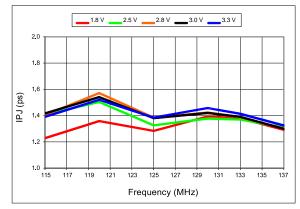


Figure 14. RMS Integrated Phase Jitter Random (12 kHz to 20 MHz) vs Frequency<sup>[9]</sup>

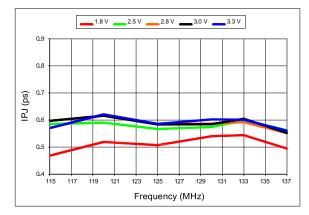


Figure 15. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency<sup>[9]</sup>

#### Notes:

- 8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
- 9. Phase noise plots are measured with Agilent E5052B signal source analyzer.



## **Programmable Drive Strength**

The MO8009 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, contact KDS.

#### **EMI Reduction by Slowing Rise/Fall Time**

Figure 16 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

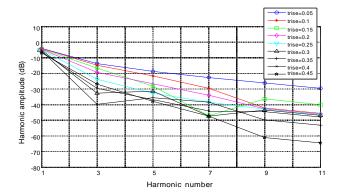


Figure 16. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

#### Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to speed up the rise/fall time of the input clock. Some chipsets may also require faster rise/fall time in order to reduce their sensitivity to this type of jitter. Refer to the Rise/Fall Time Tables (Table 7 to Table 11) to determine the proper drive strength.

#### **High Output Load Capability**

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a +3.3V MO8009 device with default drive strength setting, the typical rise/fall time is 0.46 ns for 5 pF output load. The typical rise/fall time slows down to 1 ns when the output load increases to 15 pF. One can choose to speed up the rise/fall time to 0.72 ns by then increasing the driven strength setting on the MO8009 to "F."

The MO8009 can support up to 30 pF or higher in maximum capacitive loads with up to 3 additional drive strength settings. Refer to the Rise/Tall Time Tables (Table 7 to 11) to determine the proper drive strength for the desired combination of output load vs. rise/fall time

#### MO8009 Drive Strength Selection

Tables 7 through 11 define the rise/fall time for a given capacitive load and supply voltage.

- 1. Select the table that matches the MO8009 nominal supply voltage (+1.8V, +2.5V, +2.8V, +3.0V, +3.3V).
- 2. Select the capacitive load column that matches the application requirement (5 pF to 30 pF)
- 3. Under the capacitive load column, select the desired rise/fall times.
- 4. The left-most column represents the part number code for the corresponding drive strength.
- Add the drive strength code to the part number for ordering purposes.

Calculating Maximum Frequency

Based on the rise and fall time data given in Tables 7 through 11, the maximum frequency the oscillator can operate with guaranteed full swing of the output voltage over temperature as follows:

Max Frequency = 
$$\frac{1}{5 \times Trf_{20/80}}$$

where Trf\_20/80 is the typical value for 20%-80% rise/fall time

#### Example 1

Calculate f<sub>MAX</sub> for the following condition:

- Vdd = +3.3V (Table 11)
- · Capacitive Load: 30 pF
- Desired Tr/f time = 1.46 ns (rise/fall time part number code = U)

Part number for the above example:

MO8009IG4-CUH-33E0-0136986300



Drive strength code is here.



## Rise/Fall Time (20% to 80%) vs C<sub>LOAD</sub> Tables

Table 7. Vdd = +1.8V Rise/Fall Times for Specific C<sub>LOAD</sub>

Rise/Fall Time Typ (ns)						
Drive Strength \ C <sub>LOAD</sub> 5 pF 15 pF 30 pF						
Т	0.93	n/a	n/a			
E	0.78	n/a	n/a			
U	0.70	1.48	n/a			
F or "0": default	0.65	1.30	n/a			

Table 8. Vdd = +2.5V Rise/Fall Times for Specific C<sub>LOAD</sub>

Rise/Fall Time Typ (ns)					
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF		
R	1.45	n/a	n/a		
В	1.09	n/a	n/a		
Т	0.62	1.28	n/a		
E	0.54	1.00	n/a		
U or "0": default	0.43	0.96	n/a		
F	0.34	0.88	n/a		

Table 9. Vdd = +2.8V Rise/Fall Times for Specific C<sub>LOAD</sub>

Rise/Fall Time Typ (ns)					
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF		
R	1.29	n/a	n/a		
В	0.97	n/a	n/a		
Т	0.55	1.12	n/a		
E	0.44	1.00	n/a		
U or "0": default	0.34	0.88	n/a		
F	0.29	0.81	1.48		

Table 10. Vdd = +3.0V Rise/Fall Times for Specific C<sub>LOAD</sub>

Rise/Fall Time Typ (ns)							
Drive Strength \ C <sub>LOAD</sub> 5 pF 15 pF 30 pF							
R	1.22	n/a	n/a				
В	0.89	n/a	n/a				
T or "0": default	0.51	1.00	n/a				
E	0.38	0.92	n/a				
U	0.30	0.83	n/a				
F	0.27	0.76	1.39				

Table 11. Vdd = +3.3V Rise/Fall Times for Specific C<sub>LOAD</sub>

Rise/Fall Time Typ (ns)							
Drive Strength \ C <sub>LOAD</sub> 5 pF 15 pF 30 pF							
R	1.16	n/a	n/a				
В	0.81	n/a	n/a				
T or "0": default	0.46	1.00	n/a				
E	0.33	0.87	n/a				
U	0.28	0.79	1.46				
F	0.25	0.72	1.31				

#### Note

<sup>10. &</sup>quot;n/a" in Table 7 to Table 11 indicates that the resulting rise/fall time from the respective combination of the drive strength and output load does not provide rail-to-rail swing and is not available.



## Pin 1 Configuration Options (OE, ST, or NC)

Pin 1 of the MO8009 can be factory-programmed to support three modes: Output enable (OE), standby (ST) or No Connect (NC). These modes can also be programmed with the Time Machine using field programmable devices.

### Output Enable (OE) Mode

In the OE mode, applying logic Low to the OE pin only disables the output driver and puts it in Hi-Z mode. The core of the device continues to operate normally. Power consumption is reduced due to the inactivity of the output. When the OE pin is pulled High, the output is typically enabled in<1µs.

## Standby (ST) Mode

In the  $\overline{ST}$  mode, a device enters into the standby mode when Pin 1 pulled Low. All internal circuits of the device are turned off. The current is reduced to a standby current, typically in the range of a few  $\mu A$ . When  $\overline{ST}$  is pulled High, the device goes through the "resume" process, which can take up to 5 ms.

#### No Connect (NC) Mode

In the NC mode, the device always operates in its normal mode and output the specified frequency regardless of the logic level on pin 1.

Table 12 below summarizes the <u>key</u> relevant parameters in the operation of the device in OE, ST, or NC mode.

Table 12. OE vs. ST vs. NC

	OE	ST	NC
Active current 125 MHz (max, +1.8V)	+5.6 mA	+5.6 mA	+5.6 mA
OE disable current (max. +1.8V)	+4.0 mA	N/A	N/A
Standby current (typical +1.8V)	N/A	+0.6 µA	N/A
OE enable time at 125 MHz (max)	124 ns	N/A	N/A
Resume time from standby (max, all frequency)	N/A	5.0 ms	N/A
Output driver in OE disable/standby mode	High Z	weak pull-down	N/A

#### **Output on Startup and Resume**

The MO8009 comes with gated output. Its clock output is accurate to the rated frequency stability within the first pulse from initial device startup or resume from the standby mode.

In addition, the MO8009 has NO RUNT, NO GLITCH output during startup or resume as shown in the waveform captures in Figure 17 and Figure 18.

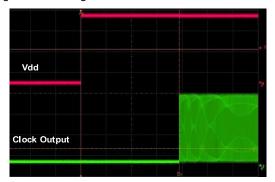


Figure 17. Startup Waveform vs. Vdd

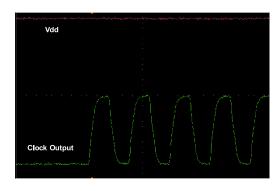


Figure 18. Startup Waveform vs. Vdd (Zoomed-in View of Figure 17)

# Instant Samples with Time Machine and Field Programmable Oscillators

KDS supports a field programmable version of the MO8009 high frequency, high temperature oscillator for fast prototyping and real time customization of features. The field programmable devices (FP devices) are available for all five standard MO8009 package sizes and can be configured to one's exact specification using the Time Machine II, an USB powered MEMS oscillator programmer.

#### Customizable Features of the MO8009 FP Devices Include

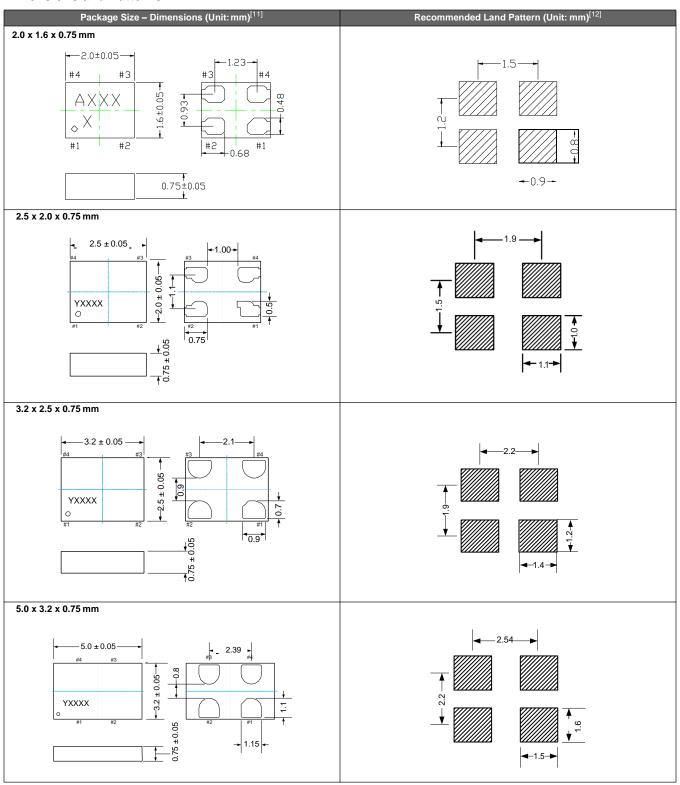
- Frequencies between 115 MHz 137 MHz
- Three frequency stability options, ±20 ppm, ±25 ppm, ±50 ppm
- Two operating temperatures, -20 to +70°C or -40 to +85°C
- Six supply voltage options, +1.8V, +2.5V, +2.8V, +3.0V, +3.3V and+2.25 to +3.63V continuous
- · Output drive strength
- · OE, ST, or NC mode

For more information regarding KDS's field programmable solutions, contact KDS.

MO8009 is factory-programmed per customer ordering codes for volume delivery.



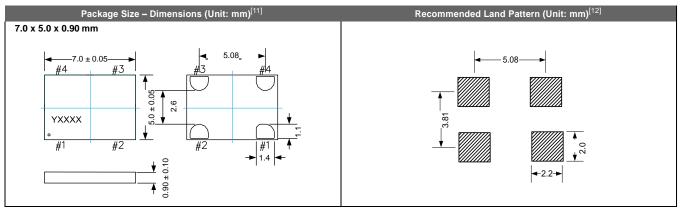
### **Dimensions and Patterns**



## MO8009 High Frequency, Low Power Oscillator



### **Dimensions and Patterns**



#### Notes:

- 11. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
- 12. A capacitor of value 0.1  $\mu F$  or higher between Vdd and GND is required.



#### **Ordering Information**

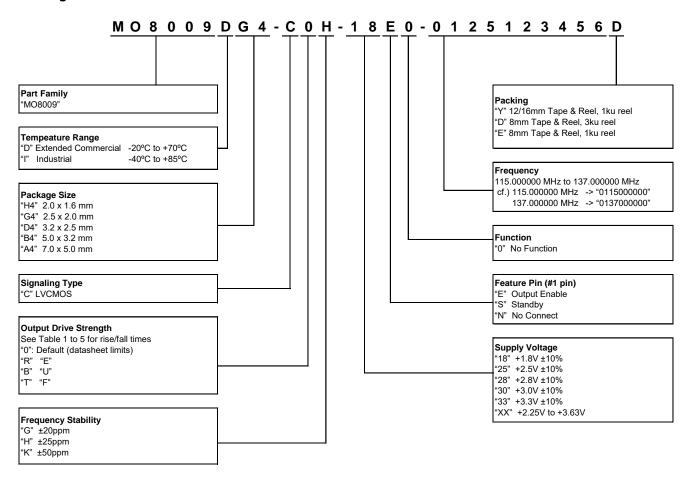


Table 13. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	16 mm T&R (3ku)	16 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	8 mm T&R (3ku)	8 mm T&R (1ku)
2.0 x 1.6	_	-	ı	Ī	D	E
2.5 x 2.0	_	-	ı	Ī	D	E
3.2 x 2.5	_	-	_	-	D	E
5.0 x 3.2	_	-	_	Υ	-	-
7.0 x 5.0	_	Υ	_	_	_	_

# MO8009 High Frequency, Low Power Oscillator



## **Revision History**

## Table 14 Datasheet Version and Change Log

Version	Release Date	Change Summary
1.0	06/10/2014	Final production release
1.01	05/07/2015	Revised the Electrical Characteristics, Timing Diagrams and Performance Plots     Revised 2016 package diagram
1.02	06/18/2015	Added 16 mm T&R information to Table 13     Revised 12 mm T&R information to Table 13
1.03	08/30/2016	Revised part number example in the ordering information
1.04	01/11/2017	Revised 2520 package land pattern